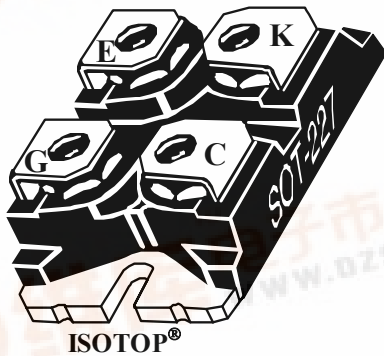
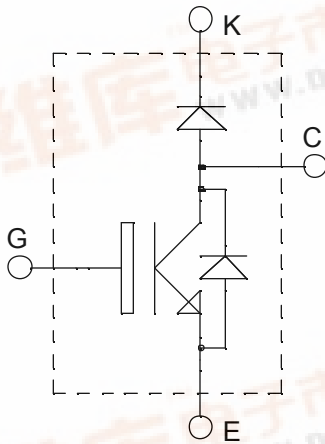




APT50GT120JU2

**ISOTOP[®] Boost chopper
Trench + Field Stop IGBT[®]**

**$V_{CES} = 1200V$
 $I_C = 50A @ T_c = 80^\circ C$**



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- Trench + Field Stop IGBT[®] Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- ISOTOP[®] Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CESat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V	
I_{C1}	Continuous Collector Current	$T_C = 25^\circ C$	75	
I_{C2}		$T_C = 80^\circ C$	50	
I_{CM}		Pulsed Collector Current	$T_C = 25^\circ C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V	
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	347	
$I_{F_{AV}}$	Maximum Average Forward Current	Duty cycle=0.5	$T_C = 80^\circ C$	27
$I_{F_{RMS}}$	RMS Forward Current (Square wave, 50% duty)			34

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1200\text{V}$			5	mA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 50\text{A}$	$T_j = 25^\circ\text{C}$ 1.4	1.7	2.1	V
			$T_j = 125^\circ\text{C}$ 2.0			
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2\text{mA}$	5.0		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$			500	nA

Dynamic Characteristics

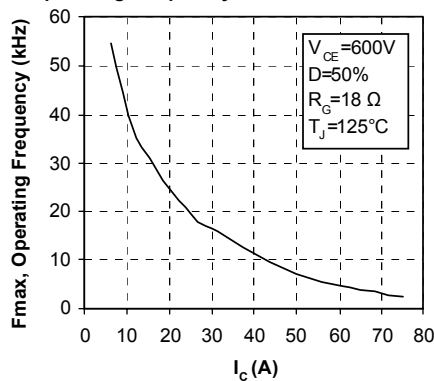
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		3600		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		188		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		163		
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching (25°C)		85		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$		30		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50\text{A}$		420		
T_f	Fall Time	$R_G = 18\Omega$		65		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		90		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$		45		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50\text{A}$		520		
T_f	Fall Time	$R_G = 18\Omega$		90		
E_{on}	Turn-on Switching Energy			6.6		mJ
E_{off}	Turn-off Switching Energy			5.8		

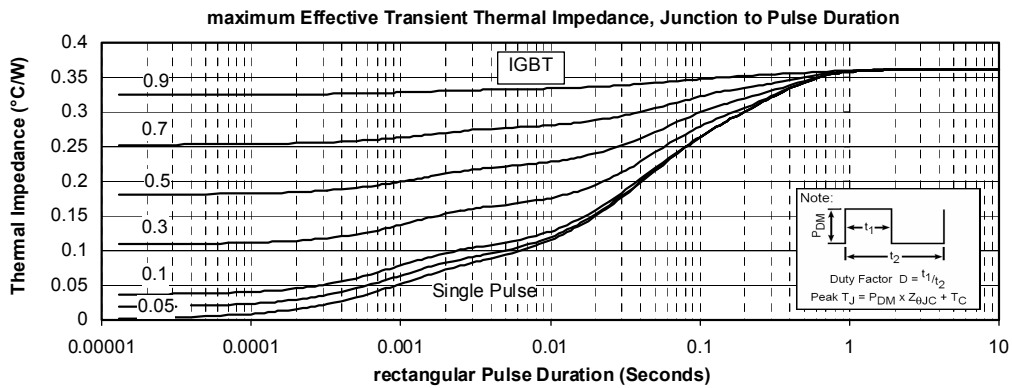
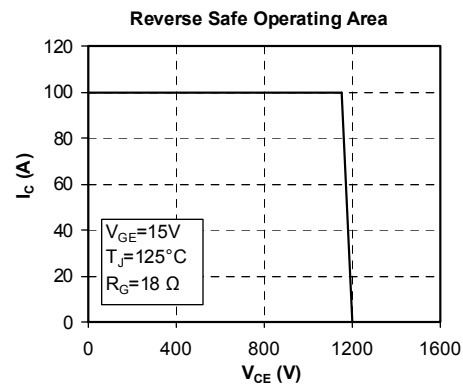
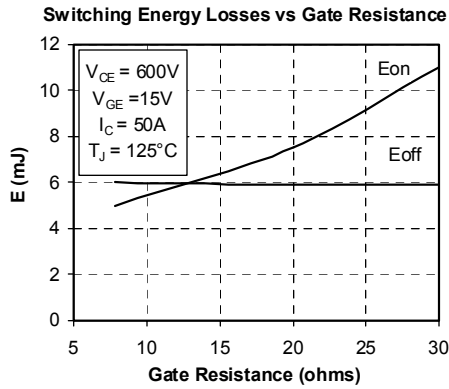
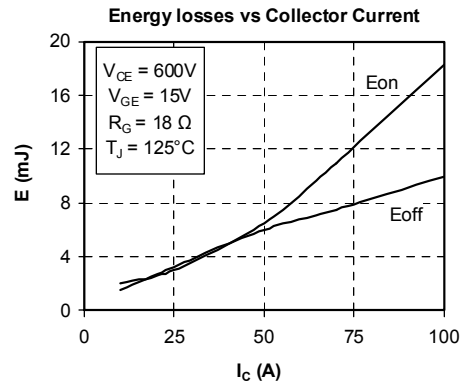
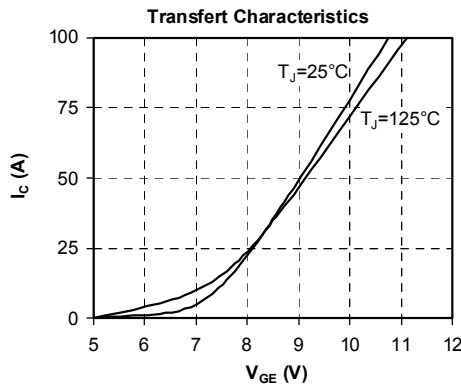
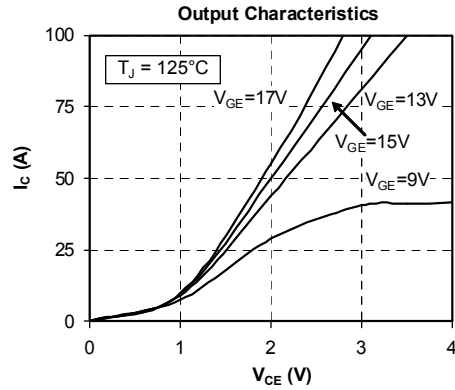
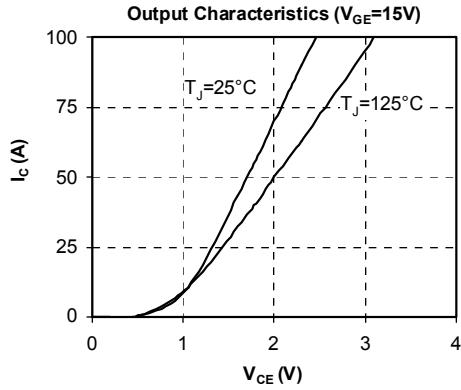
Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 30A$		2.0	2.5	V
		$I_F = 60A$		2.3		
		$I_F = 30A$ $T_j = 125^\circ C$		1.8		
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$ $T_j = 25^\circ C$			250	μA
		$V_R = 1200V$ $T_j = 125^\circ C$			500	
C_T	Junction Capacitance	$V_R = 200V$		32		pF
t_{rr}	Reverse Recovery Time	$I_F = 1A, V_R = 30V$ $di/dt = 100A/\mu s$	$T_j = 25^\circ C$		31	ns
	Reverse Recovery Time		$T_j = 25^\circ C$		370	
I_{RRM}	Maximum Reverse Recovery Current	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 125^\circ C$		500	A
			$T_j = 25^\circ C$		5	
Q_{rr}	Reverse Recovery Charge		$T_j = 125^\circ C$		12	nC
			$T_j = 25^\circ C$		660	
t_{rr}	Reverse Recovery Time	$I_F = 30A$	$T_j = 125^\circ C$		220	ns
Q_{rr}	Reverse Recovery Charge	$V_R = 800V$			4650	nC
I_{RRM}	Maximum Reverse Recovery Current	$di/dt = 1000A/\mu s$			37	A

Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	IGBT			0.36	$^\circ C/W$
		Diode			1.1	
R_{thJA}	Junction to Ambient (IGBT & Diode)				20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1$ min, $I_{isol} < 1mA$, 50/60Hz		2500			V
T_J, T_{STG}	Storage Temperature Range		-55		150	$^\circ C$
T_L	Max Lead Temp for Soldering: 0.063" from case for 10 sec				300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

Typical IGBT Performance Curve
Operating Frequency vs Collector Current




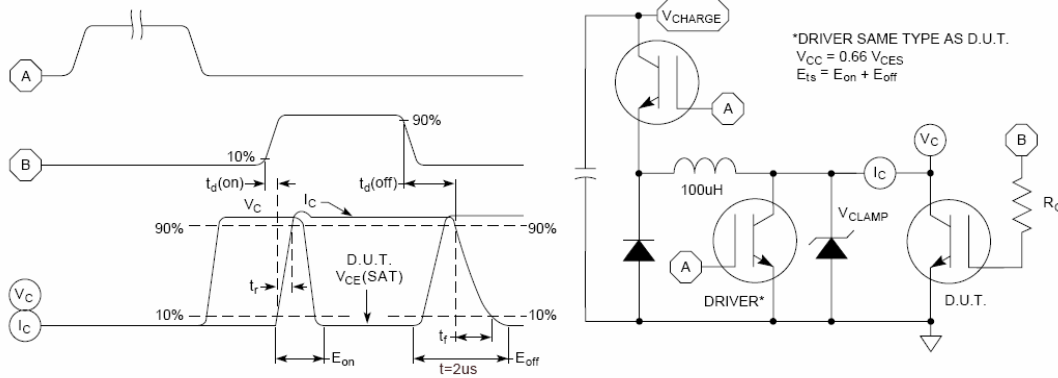


Figure 15. Switching Loss Test Circuit and Waveforms

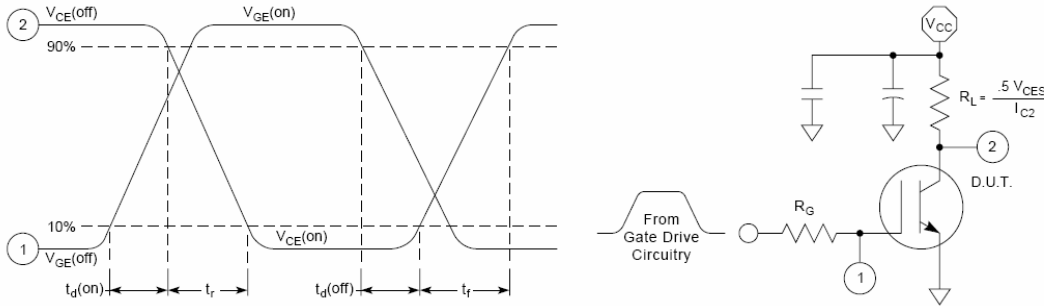


Figure 16. Resistive Switching Time Test Circuit and Waveforms

Typical Diode Performance Curve

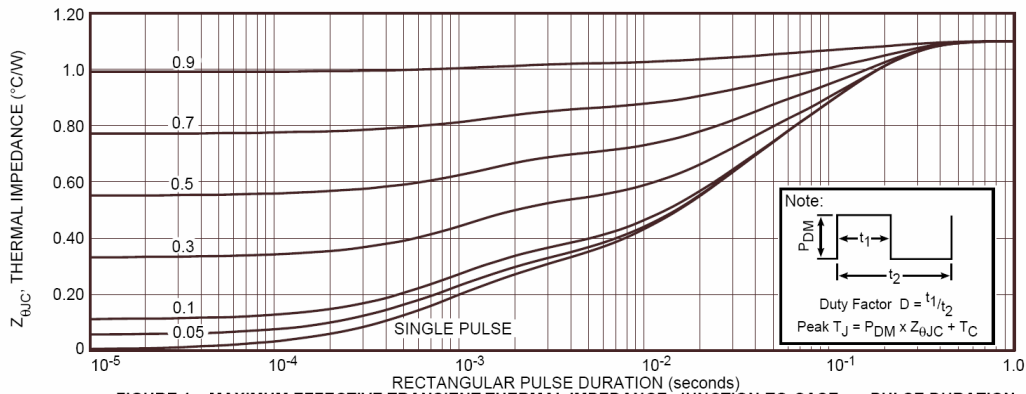


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

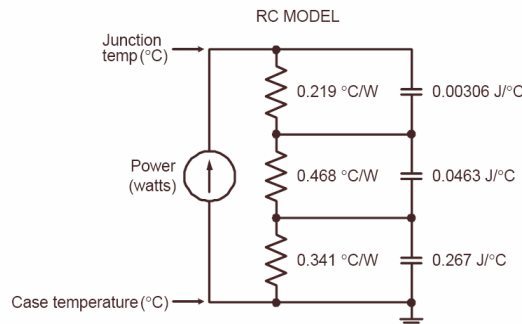


FIGURE 1b. TRANSIENT THERMAL IMPEDANCE MODEL

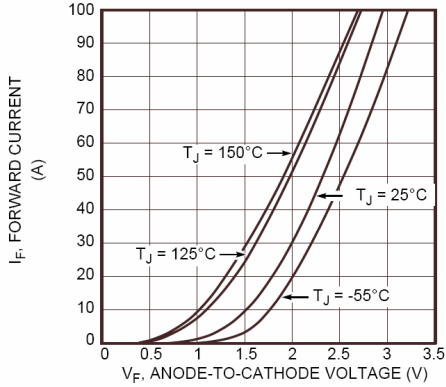


Figure 2. Forward Current vs. Forward Voltage

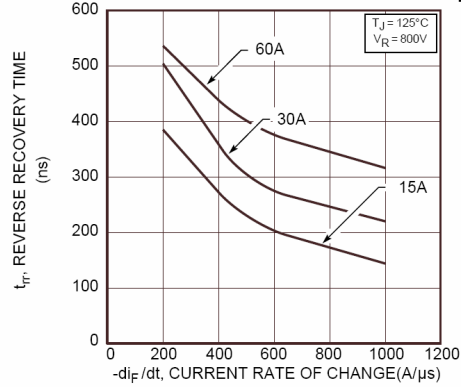


Figure 3. Reverse Recovery Time vs. Current Rate of Change

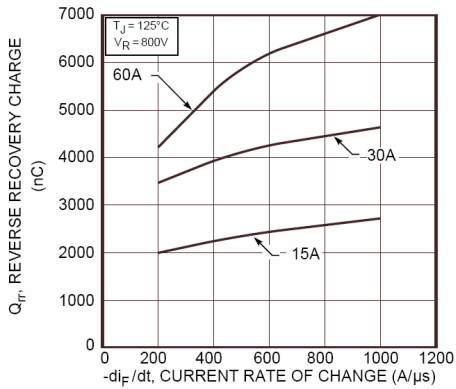


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

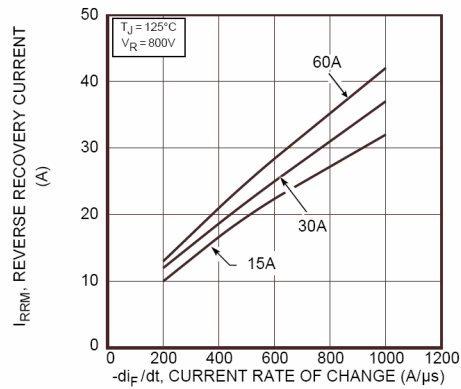


Figure 5. Reverse Recovery Current vs. Current Rate of Change

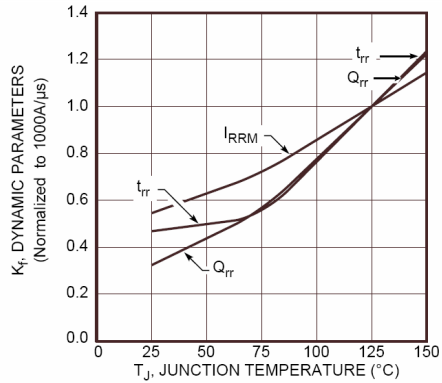


Figure 6. Dynamic Parameters vs. Junction Temperature

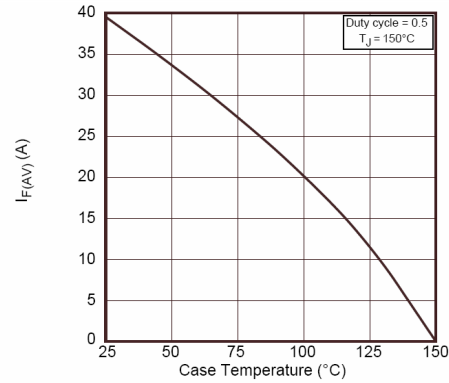


Figure 7. Maximum Average Forward Current vs. Case Temperature

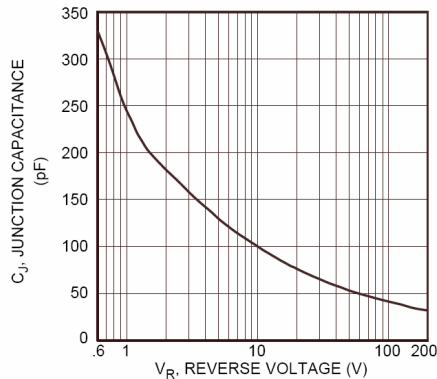


Figure 8. Junction Capacitance vs. Reverse Voltage

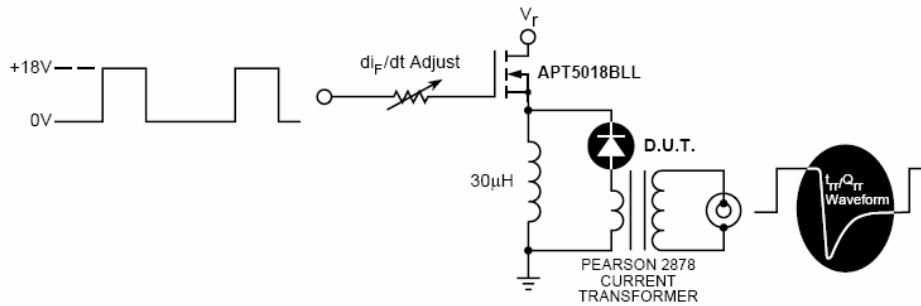


Figure 9. Diode Test Circuit

- ❶ I_F - Forward Conduction Current
- ❷ di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- ❸ I_{RRM} - Maximum Reverse Recovery Current.
- ❹ t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- ❺ Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

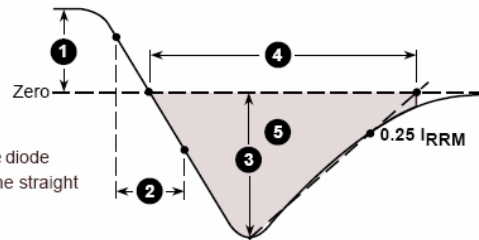
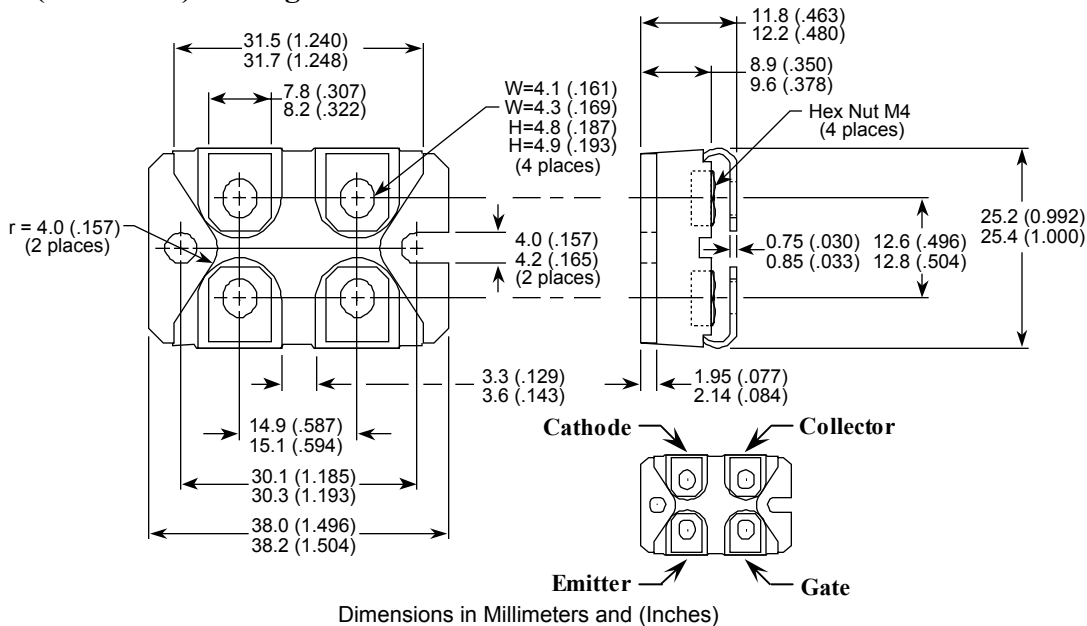


Figure 10. Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP[®]) Package Outline



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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.